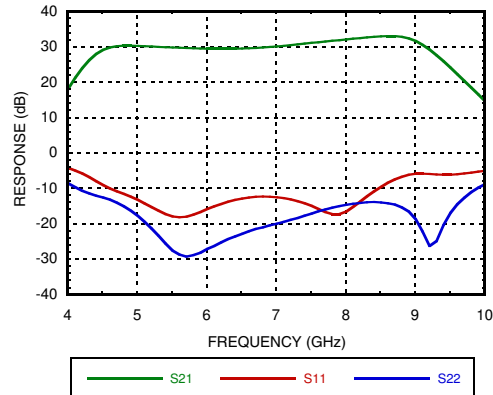
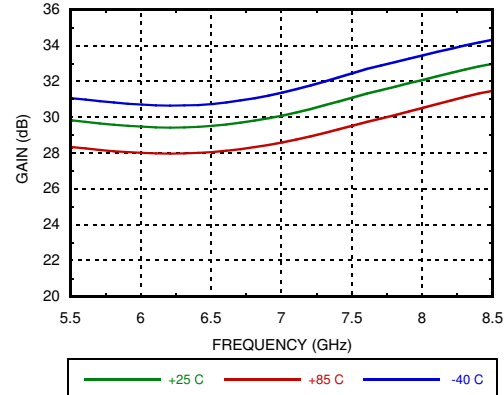


**GaAs pHEMT MMIC 2 WATT
POWER AMPLIFIER, 5.5 - 8.5 GHz**

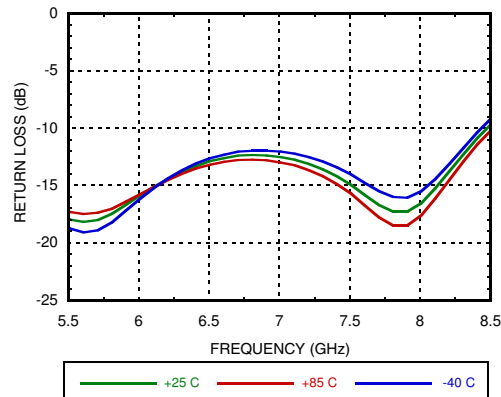
Gain & Return Loss



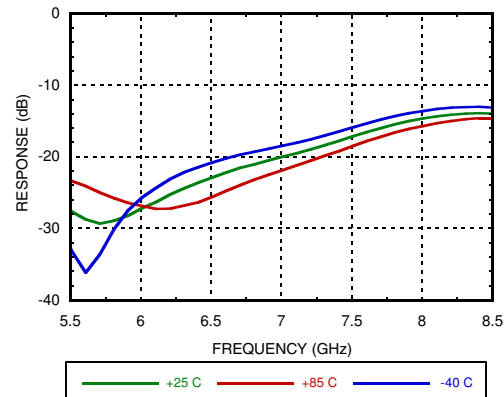
Gain vs. Temperature



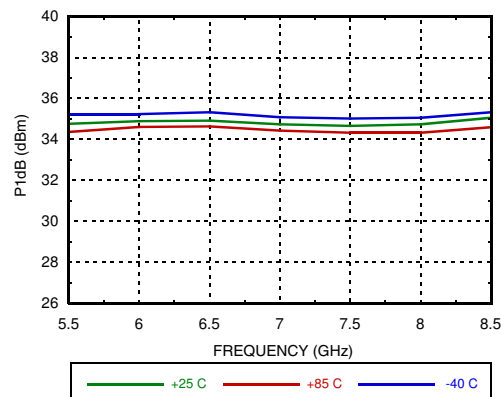
Input Return Loss vs. Temperature



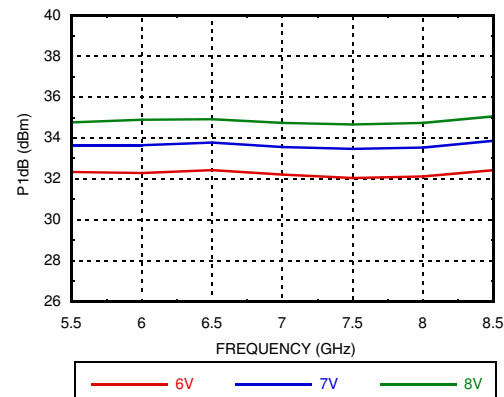
Output Return Loss vs. Temperature



P1dB vs. Temperature

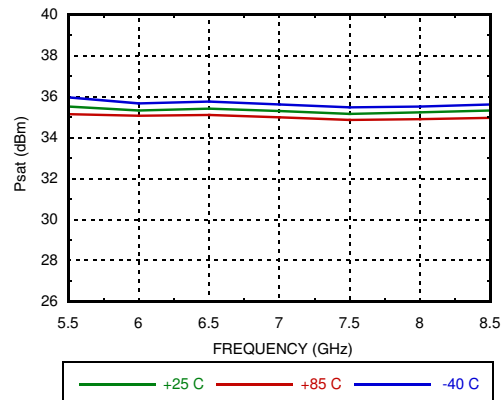


P1dB vs. Supply Voltage

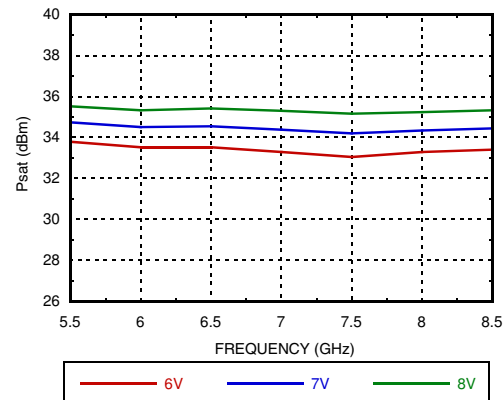


**GaAs pHEMT MMIC 2 WATT
POWER AMPLIFIER, 5.5 - 8.5 GHz**

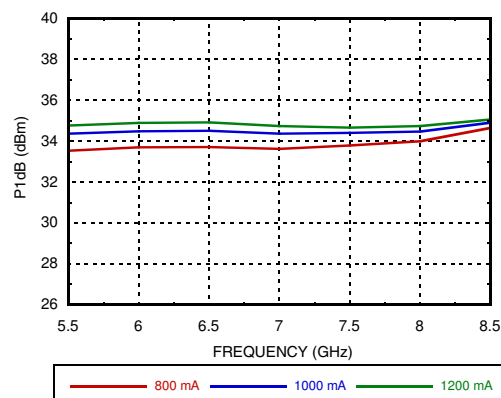
Psat vs. Temperature



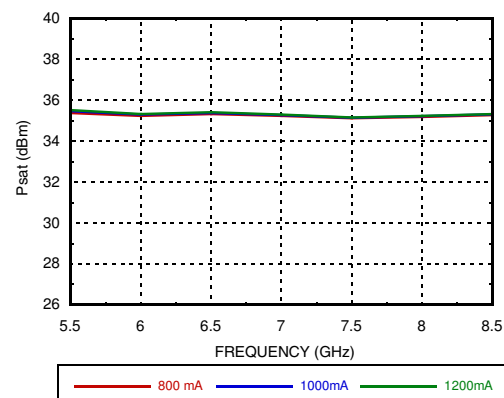
Psat vs. Supply Voltage



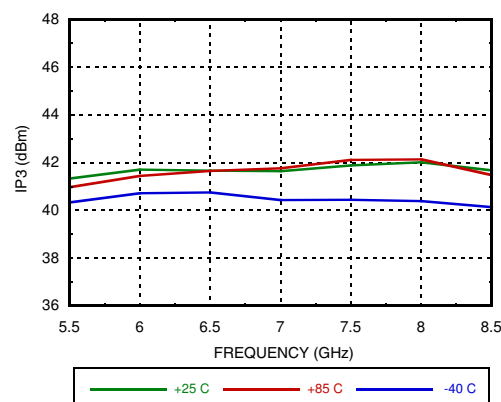
P1dB vs. Supply Current



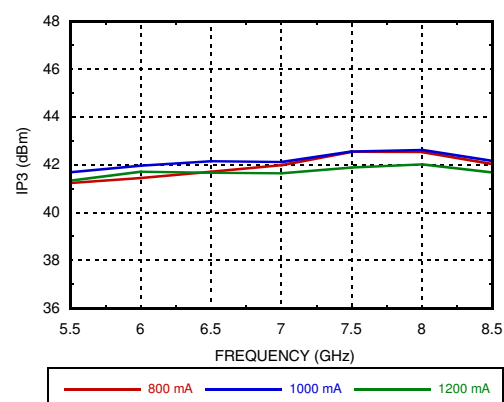
Psat vs. Supply Current



**Output IP3 vs. Temperature,
Pout/tone = +20 dBm**

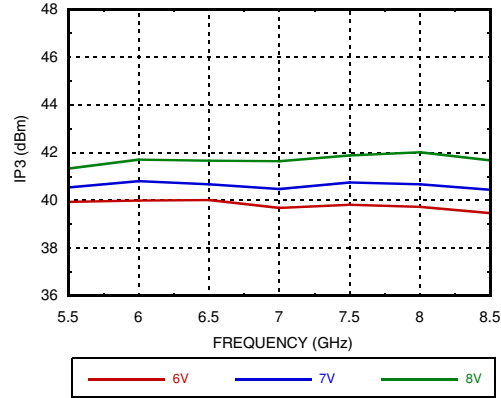


**Output IP3 vs. Supply Current,
Pout/tone = +20 dBm**

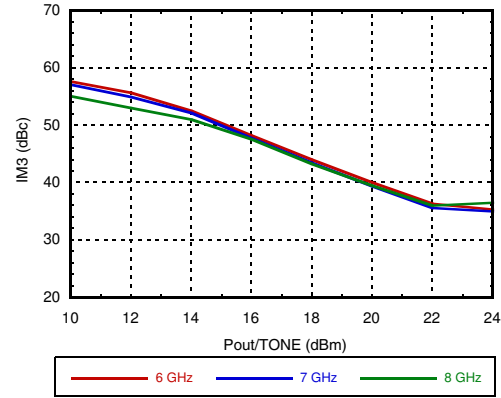


GaAs pHEMT MMIC 2 WATT POWER AMPLIFIER, 5.5 - 8.5 GHz

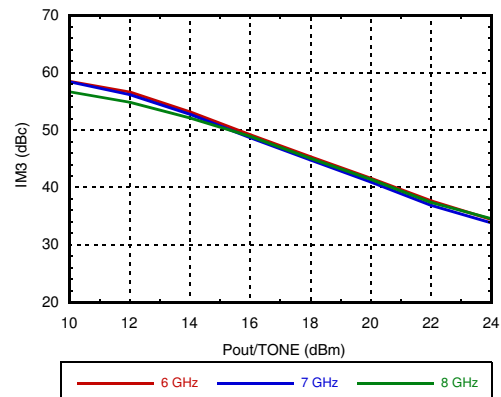
**Output IP3 vs. Supply Voltage,
Pout/tone = +20 dBm**



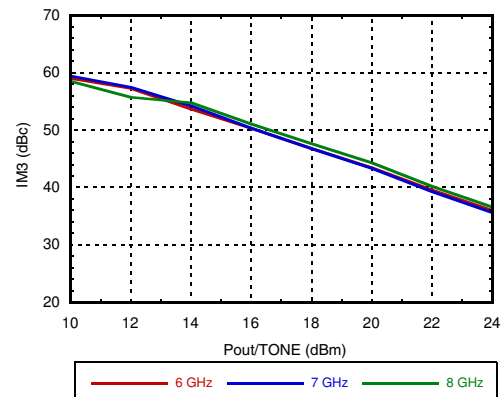
Output IM3 @ Vdd = +6V



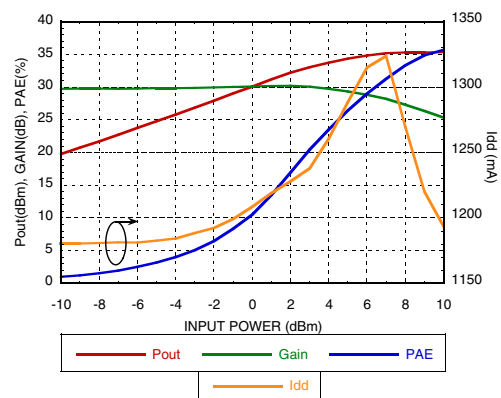
Output IM3 @ Vdd = +7V



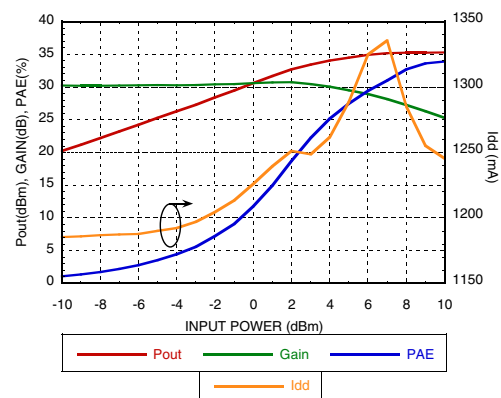
Output IM3 @ Vdd = +8V



Power Compression @ 6 GHz

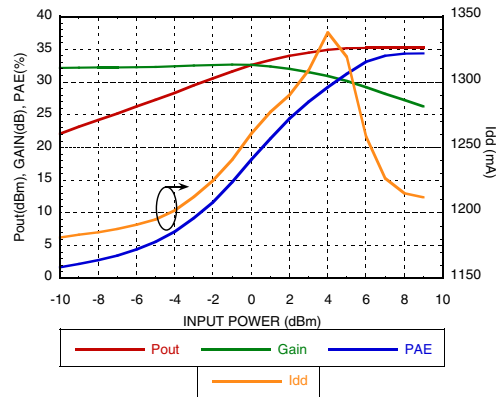


Power Compression @ 7 GHz

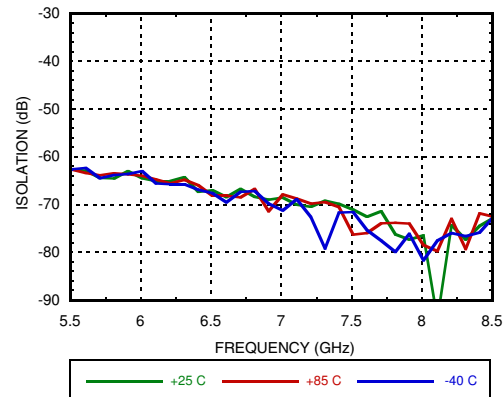


**GaAs pHEMT MMIC 2 WATT
POWER AMPLIFIER, 5.5 - 8.5 GHz**

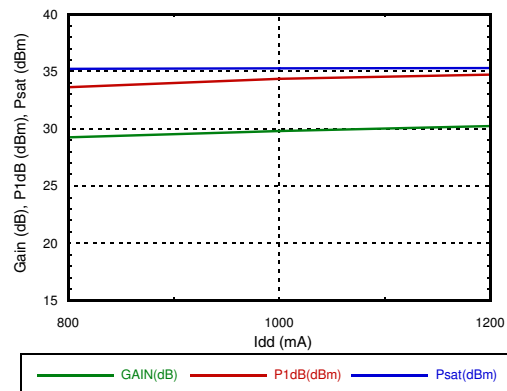
Power Compression @ 8 GHz



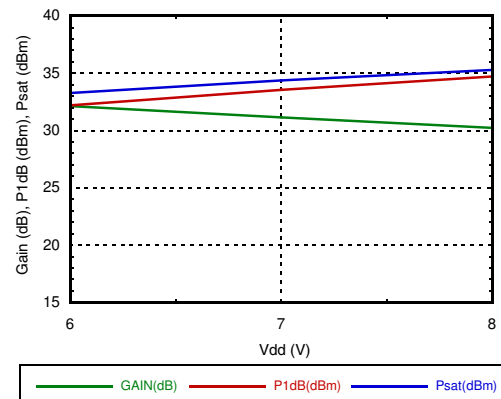
Reverse Isolation vs. Temperature



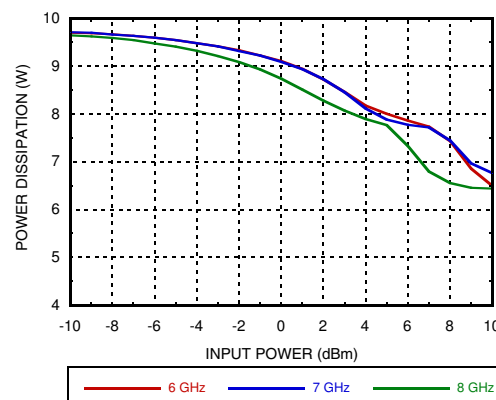
**Gain & Power vs.
Supply Current @ 7 GHz**



**Gain & Power vs.
Supply Voltage @ 7 GHz**



Power Dissipation



GaAs pHEMT MMIC 2 WATT POWER AMPLIFIER, 5.5 - 8.5 GHz

Absolute Maximum Ratings

Drain Bias Voltage (Vdd)	+9 Vdc
Gate Bias Voltage (Vgg)	-2 to -0.4 Vdc
RF Input Power (RFIN)	+22 dBm
Channel Temperature	175 °C
Continuous P _{diss} (T= 85 °C) (derate 135mW/°C above 85 °C)	12.2 W
Thermal Resistance (channel to ground paddle)	7.38 °C/W
Storage Temperature	-65 to 150 °C
Operating Temperature	-40 to 85 °C
ESD Sensitivity (HBM)	Class 1A, passed 250V

Typical Supply Current vs. Vdd

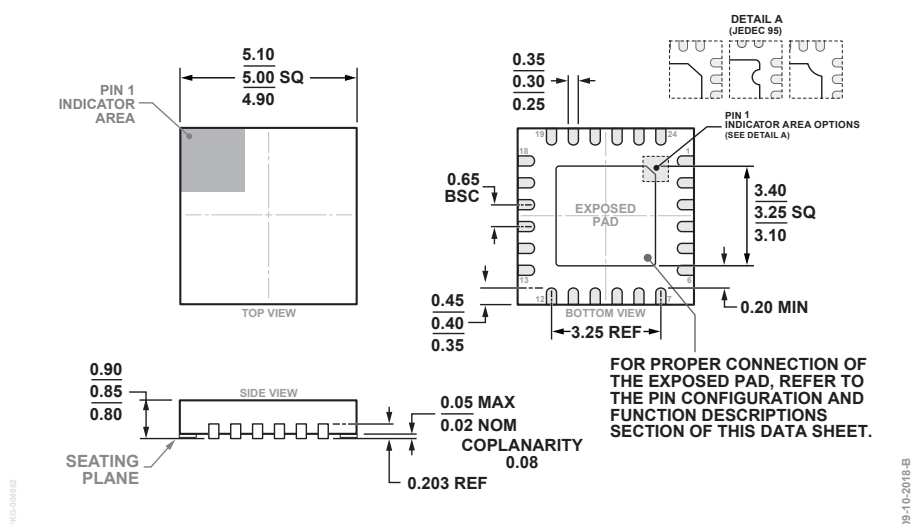
Vdd (V)	Idd (mA)
+6	1200
+7	1200
+8	1200

Adjust Vgg to achieve Idd = 1200 mA



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing



24-Lead Lead Frame Chip Scale Package [LFCSP]
5 mm x 5 mm Body and 0.85 mm Package Height
(CP-24-20)
Dimensions shown in millimeters.

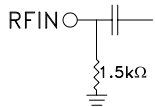
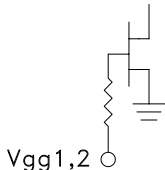
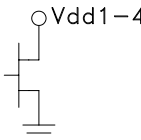
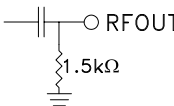
Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating [2]	Package Marking [1]
HMC7357LP5GE	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL3	H7357 XXXX

[1] 4-Digit lot number XXXX

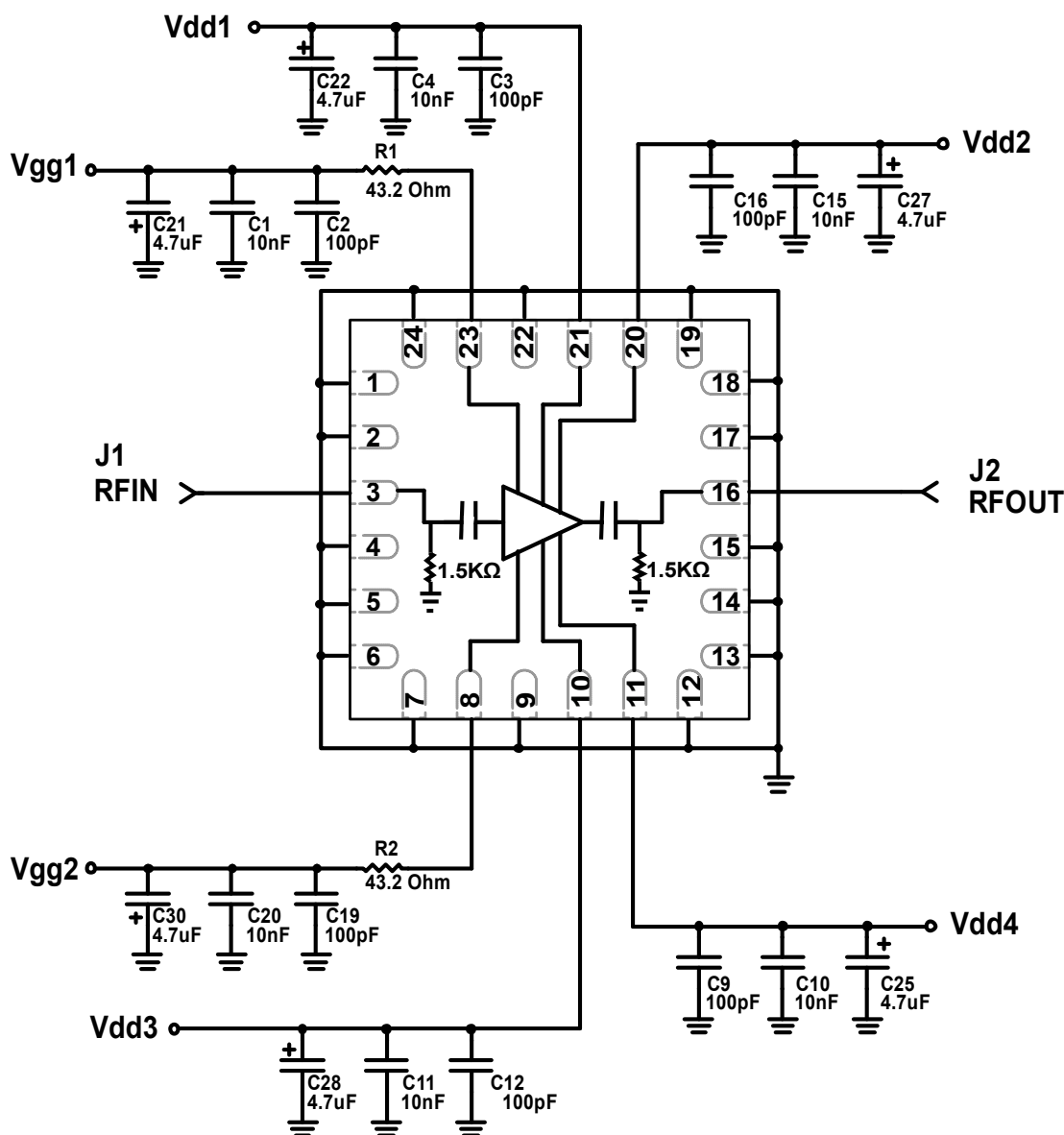
[2] Max peak reflow temperature of 260 °C

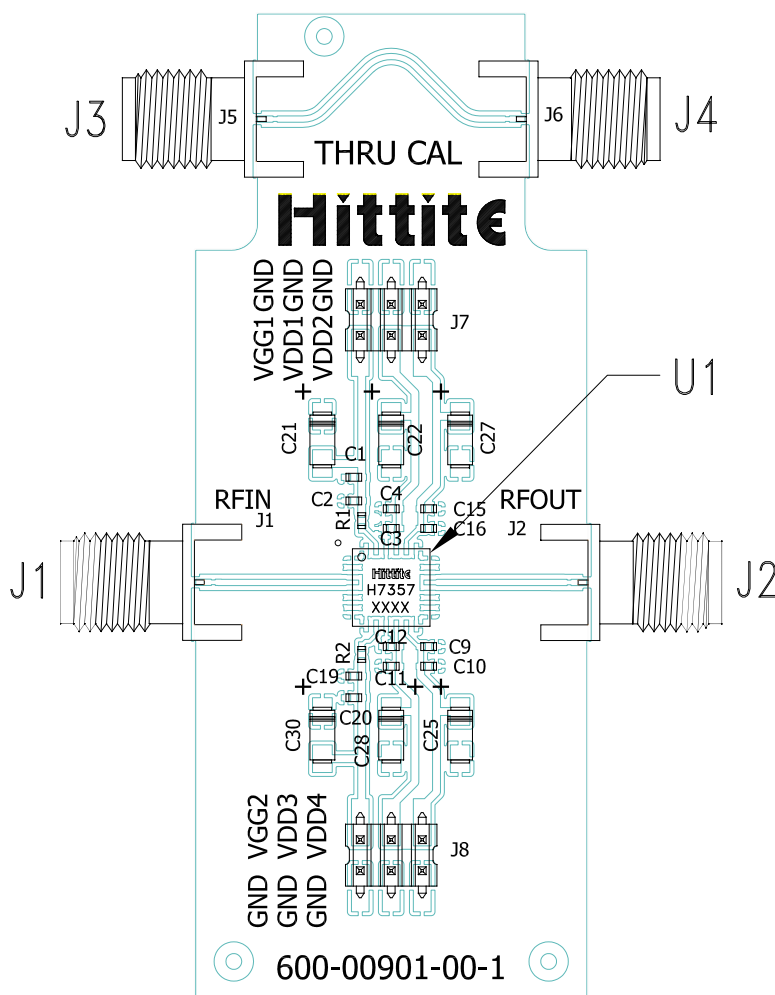
**GaAs pHEMT MMIC 2 WATT
POWER AMPLIFIER, 5.5 - 8.5 GHz**
Pin Descriptions

Pad Number	Function	Description	Interface Schematic
1, 4, 5, 6, 7, 9, 12, 13, 14, 17, 18, 19, 22, 24	N/C	These pins are not connected internally; however all data shown herein was measured with these pins connected to RF/DC ground externally.	
2, 15	GND	These pins and exposed ground paddle must be connected to RF/DC ground.	
3	RFIN	This pin is DC coupled and matched to 50 Ohms.	
8, 23	Vgg2, Vgg1	Gate control for PA. Adjust Vgg to achieve recommended bias current. External bypass capacitors of 100 pF, 10 nF, and 4.7 μF are required. Apply Vgg bias to either pin 8 or pin 23.	
10, 11, 20, 21	Vdd3, Vdd4, Vdd2, Vdd1	Drain bias voltage for the amplifier. External bypass capacitors of 100 pF, 10 nF, and 4.7 μF are required.	
16	RFOUT	This pin is DC coupled and matched to 50 Ohms.	

**GaAs pHEMT MMIC 2 WATT
POWER AMPLIFIER, 5.5 - 8.5 GHz**

Application Circuit



**GaAs pHEMT MMIC 2 WATT
POWER AMPLIFIER, 5.5 - 8.5 GHz**
Evaluation PCB

List of Materials for Evaluation PCB EV1HMC7357LP5 ^[1]

Item	Description
J1 - J4	"K" Connector, SRI
J7, J8	DC Pin
C2, C3, C9, C12, C16, C19	100 pF Capacitor, 0402 Pkg.
C1, C4, C10, C11, C15, C20	10000 pF Capacitor, 0402 Pkg.
C21, C22, C25, C27, C28, C30	4.7 uF Capacitor, Case A Pkg.
R1, R2	43.2 Ohm Resistor, 0402 Pkg
U1	HMC7357LP5GE Amplifier
PCB ^[2]	600-00901-00 Eval Board

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Analog Devices, upon request.



HMC7357LP5GE

v01.0918

**GaAs pHEMT MMIC 2 WATT
POWER AMPLIFIER, 5.5 - 8.5 GHz**

Notes: